

L Number	Hits	Search Text	DB	Time stamp
1	394060	((flash volatile (non-volatile) near5 memory)) EEPROM EPROM PROM E2PROM	USPAT; US-PGPUB	2004/09/13 13:34
2	13787	((flash volatile (non-volatile) near5 memory)) EEPROM EPROM PROM E2PROM) and (float\$3 near3 gate)	USPAT; US-PGPUB	2004/09/13 13:34
3	10907	((flash volatile (non-volatile) near5 memory)) EEPROM EPROM PROM E2PROM) and (float\$3 near3 gate)) and (control near3 gate)	USPAT; US-PGPUB	2004/09/13 13:01
4	5754	((flash volatile (non-volatile) near5 memory)) EEPROM EPROM PROM E2PROM) and (float\$3 near3 gate)) and (control near3 gate)) and (eth\$3 pattern\$3)	USPAT; US-PGPUB	2004/09/13 13:35
5	5755	((flash volatile (non-volatile) near5 memory)) EEPROM EPROM PROM E2PROM) and (float\$3 near3 gate)) and (control near3 gate)) and (eth\$3 pattern\$4)	USPAT; US-PGPUB	2004/09/13 13:35
6	1371	((flash volatile (non-volatile) near5 memory)) EEPROM EPROM PROM E2PROM) and (float\$3 near3 gate)) and (control near3 gate)) and (eth\$3 pattern\$4)) and (CMP (chemical near3 mechanical near3 polish\$3))	USPAT; US-PGPUB	2004/09/13 13:40
7	168516	((flash volatile (non-volatile) near5 memory)) EEPROM EPROM PROM E2PROM	EPO; JPO; DERWENT; IBM_TDB	2004/09/13 13:34
8	8007	((flash volatile (non-volatile) near5 memory)) EEPROM EPROM PROM E2PROM) and (float\$3 near3 gate)	EPO; JPO; DERWENT; IBM_TDB	2004/09/13 13:34
9	1063	((flash volatile (non-volatile) near5 memory)) EEPROM EPROM PROM E2PROM) and (float\$3 near3 gate)) and (eth\$3 pattern\$3)	EPO; JPO; DERWENT; IBM_TDB	2004/09/13 13:40
10	6621	((flash volatile (non-volatile) near5 memory)) EEPROM EPROM PROM E2PROM) and (float\$3 near3 gate)) and (control near3 gate)) and (etch\$3 pattern\$4)	USPAT; US-PGPUB	2004/09/13 13:35
12	1493	((flash volatile (non-volatile) near5 memory)) EEPROM EPROM PROM E2PROM) and (float\$3 near3 gate)) and (control near3 gate)) and (etch\$3 pattern\$4)) and (CMP (chemical near3 mechanical near3 polish\$3))	USPAT; US-PGPUB	2004/09/13 13:36
14	122	((flash volatile (non-volatile) near5 memory)) EEPROM EPROM PROM E2PROM) and (float\$3 near3 gate)) and (control near3 gate)) and (etch\$3 pattern\$4)) and (CMP (chemical near3 mechanical near3 polish\$3)) not (((flash volatile (non-volatile) near5 memory)) EEPROM EPROM PROM E2PROM) and (float\$3 near3 gate)) and (control near3 gate)) and (eth\$3 pattern\$4)) and (CMP (chemical near3 mechanical near3 polish\$3))	USPAT; US-PGPUB	2004/09/13 13:37
15	1896	((flash volatile (non-volatile) near5 memory)) EEPROM EPROM PROM E2PROM) and (float\$3 near3 gate)) and (etch\$3 pattern\$3)	EPO; JPO; DERWENT; IBM_TDB	2004/09/13 13:40
16	53	((flash volatile (non-volatile) near5 memory)) EEPROM EPROM PROM E2PROM) and (float\$3 near3 gate)) and (etch\$3 pattern\$3)) and (CMP (chemical near3 mechanical near3 polish\$3))	EPO; JPO; DERWENT; IBM_TDB	2004/09/13 13:40